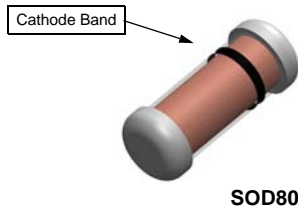




ON Semiconductor®

BAV103

High Voltage, General Purpose Diode



Description

A general purpose diode that couples high forward conductance fast swiching speed and high blocking voltages in a glass leadless LL-34 surface mount package. Placement of the expansion gap has no relationship to the location of the cathode terminal which is indicated by the first color band.

Absolute Maximum Ratings⁽¹⁾

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Units	
W_{IV}	Working Inverse Voltage	200	V	
I_O	Average Rectified Current	200	mA	
I_F	DC Forward Current	500	mA	
i_f	Recurrent Peak Forward Current	600	mA	
I_{FSM}	Non-repetitive Peak Forward Current	Pulse Width = 1.0 s	1.0	A
		Pulse Width = 1.0 μs	4.0	A
T_{STG}	Storage Temperature Range	-65 to +200	$^\circ\text{C}$	
T_J	Operating Junction Temperature	-65 to +200	$^\circ\text{C}$	

Note:

1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
	Linear Derating Factor from $T_A = 25^\circ\text{C}$	3.33	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	350	$^\circ\text{C}/\text{W}$

Electrical CharacteristicsValues are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Units
V_R	Breakdown Voltage	$I_R = 100 \mu\text{A}$	250		V
V_F	Forward Voltage	$I_F = 100 \text{ mA}$		1.00	V
		$I_F = 200 \text{ mA}$		1.25	V
I_R	Reverse Current	$V_R = 200 \text{ V}$		100	nA
		$V_R = 200 \text{ V}, T_A = 150^\circ\text{C}$		100	μA
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		5.00	pF
t_{rr}	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA}, I_{RR} = 1 \text{ mA}$ $R_L = 100 \Omega$		50	ns

Typical Performance Characteristics

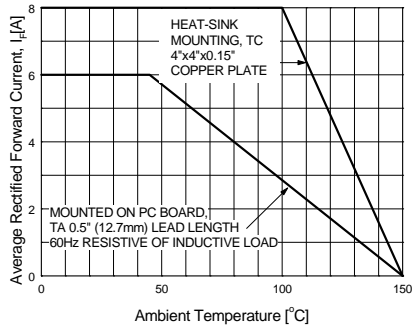


Figure 1. Forward Current Derating Curve

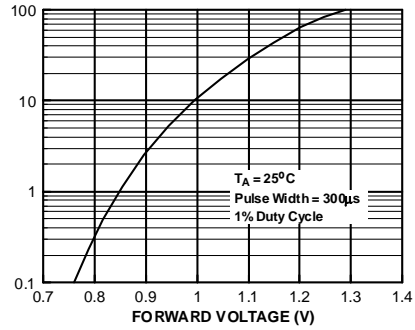


Figure 2. Forward Characteristics

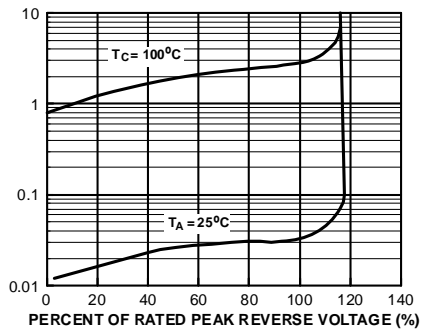


Figure 3. Reverse Characteristics

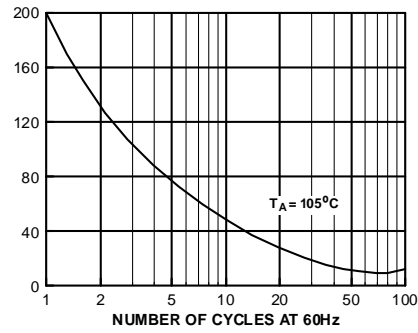


Figure 4. Non-Repetitive Surge Current

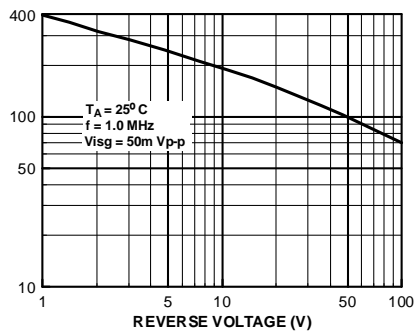
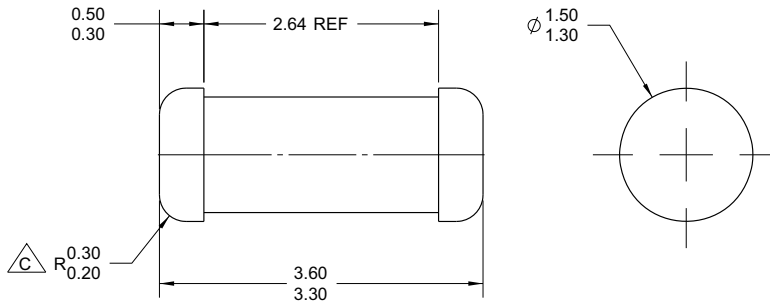


Figure 5. Junction Capacitance

Physical Dimensions

SOD-80



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) PACKAGE STANDARD REFERENCE: JEDEC DO-213, VARIATION AC.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) CORNER RADIUS IS OPTIONAL.
 - D) DRAWING FILE NAME: SOD80A REV01

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local
Sales Representative